

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











DMP6110SSDQ

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
-60V	$105m\Omega$ @ $V_{GS} = -10V$	-3.3A
-00 V	$130 \text{m}\Omega$ @ $V_{GS} = -4.5V$	-3.0A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

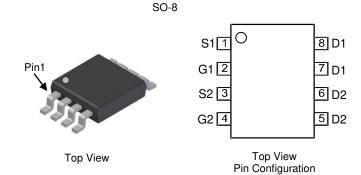
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

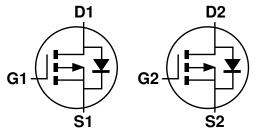
Features

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.074 grams (Approximate)





Equivalent Circuit

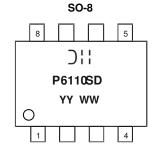
Ordering Information (Note 5)

Part Number	Case	Packaging
DMP6110SSDQ-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Oll = Manufacturer's Marking
P6110SD = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	-60	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7) V 10V	$T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$	I _D	-7.8 -6.3	Α
Continuous Drain Current (Note 7) V _{GS} = -10V	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-3.3 -2.7	Α
Pulsed Drain Current (380µs Pulse, 1% Duty Cycle)	I _{DM}	-24	Α	
Maximum Continuous Body Diode Forward Current (Note 7)	Is	-1.8	Α	
Avalanche Current (Note 10) L = 0.1mH	I _{AS}	-19	Α	
Avalanche Energy (Note 10) L = 0.1mH	Eas	18	mJ	

Thermal Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Notes 6 & 8)	T _A = +25°C		1.2	W
Total Fower Dissipation (Notes 6 & 6)	$T_A = +70$ °C	P_{D}	0.9	
Total Power Dissipation (Notes 6 & 9)	T _A = +25°C		1.2	
Thermal Resistance, Junction to Ambient (Notes 6 & 8)	Steady State		104	°C/W
Thermal resistance, buriction to Ambient (Notes 6 & 6)	t<10s	$R_{ heta JA}$	45	
Thermal Resistance, Junction to Ambient (Notes 6 & 9)	Steady State		100	
Total Power Dissipation (Notes 7 & 8)	T _A = +25°C		1.7	W
Total Fower Dissipation (Notes 7 & 6)	T _A = +70°C	P_{D}	1.1	
Total Power Dissipation (Notes 7 & 9)	T _A = +25°C		1.8	
Thermal Resistance, Junction to Ambient (Notes 7 & 8)	Steady State		74	2004
Themai hesistance, sunction to Ambient (Notes 7 & 6)	t<10s	$R_{ hetaJA}$	37	
ermal Resistance, Junction to Ambient (Notes 7 & 9) Steady Sta			71	°C/W
Thermal Resistance, Junction to Case (Notes 7 & 8)		$R_{ heta JC}$	15	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 8. For a dual device with one active die.
- 9. For a device with two active die running at equal power.
- 10. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.



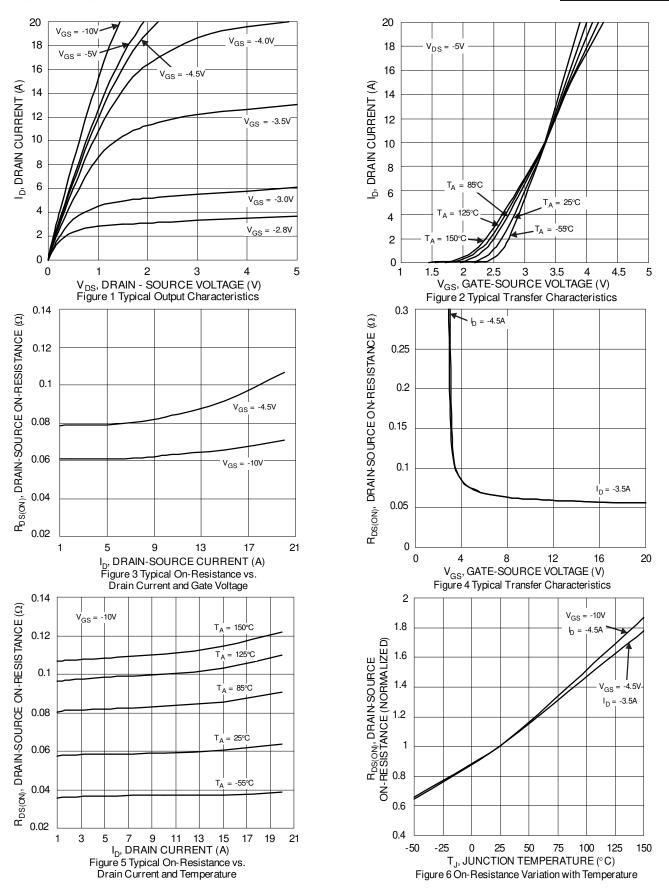
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 11)							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 11)							
Gate Threshold Voltage	V _{GS(TH)}	-1	_	-3	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance		_	80	105	mΩ	$V_{GS} = -10V, I_D = -4.5A$	
Static Drain-Source Ori-nesistance	R _{DS(ON)}	_	95	130	11122	$V_{GS} = -4.5V, I_D = -3.5A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 12)							
Input Capacitance	Ciss	_	969	_	pF		
Output Capacitance	Coss	_	57	_	pF	$V_{DS} = -30V, V_{GS} = 0V, f = 1.0MHz$	
Reverse Transfer Capacitance	C _{RSS}	_	44	_	pF		
Gate Resistance	R_{G}	_	13.7	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_{G}	_	8.2	_	nC	$V_{DS} = -30V, I_{D} = -12A$	
Total Gate Charge (V _{GS} = -10V)	Q_{G}	_	17.2	_	nC		
Gate-Source Charge	Q_{GS}	_	3.0	_	nC	$V_{DS} = -30V, I_{D} = -12A$	
Gate-Drain Charge	Q_{GD}	_	3.1	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	4.4	_	ns		
Turn-On Rise Time	t _R	_	23	_	ns	$V_{GS} = -10V, V_{DS} = -30V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	34	_	ns	$R_{GEN} = 3\Omega$, $I_{D} = -12A$	
Turn-Off Fall Time	t _F	_	42		ns	1	
Body Diode Reverse Recovery Time	t _{RR}	_	13.2	_	ns	I _S = -12A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	6.18	_	nC		

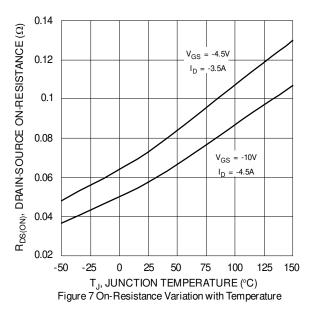
Notes:

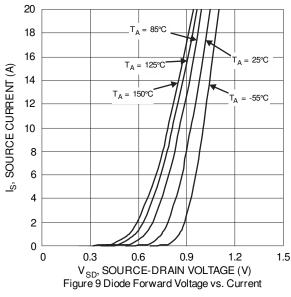
^{11.} Short duration pulse test used to minimize self-heating effect.12. Guaranteed by design. Not subject to product testing.

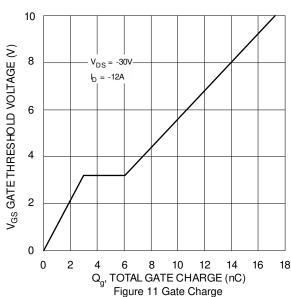


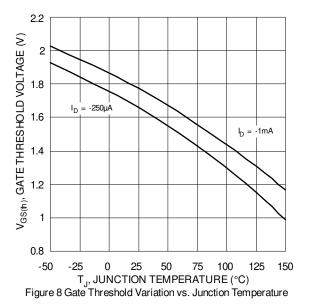


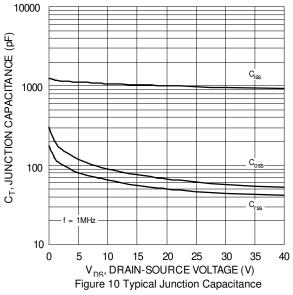


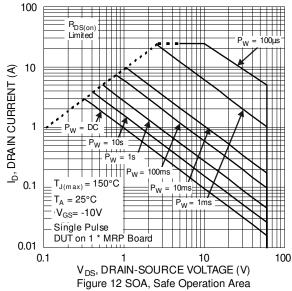




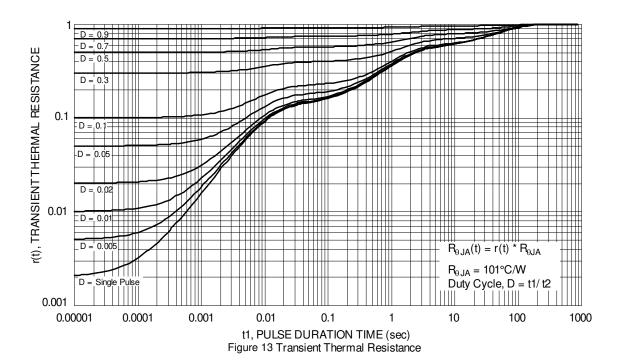










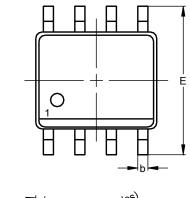


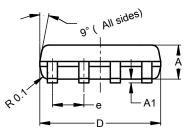


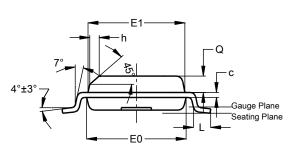
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





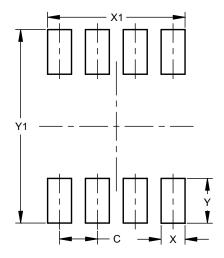


SO-8						
Dim	Min	Max	Тур			
Α	1.40	1.50	1.45			
A 1	0.10	0.20	0.15			
p	0.30	0.50	0.40			
С	0.15	0.25	0.20			
D	4.85	4.95	4.90			
Е	5.90	6.10	6.00			
E1	3.80	3.90	3.85			
E0	3.85	3.95	3.90			
е			1.27			
h	-		0.35			
L	0.62	0.82	0.72			
Ø	0.60	0.70	0.65			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)			
С	1.27			
X	0.802			
X1	4.612			
Υ	1.505			
Y1	6.50			



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2016, Diodes Incorporated

www.diodes.com